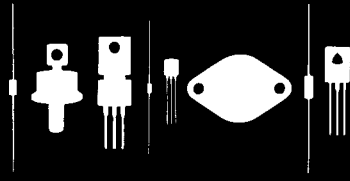


Central
Semiconductor Corp.

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145 Adams Avenue
Hauppauge, New York 11788



2N3641 PN3641
2N3642 PN3642
2N3643 PN3643

JEDEC TO-105 JEDEC TO-92

NPN SILICON SIGNAL TRANSISTORS

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3641, PN3641 Series types are Silicon NPN Small Signal Transistors designed for general purpose amplifier applications.

MAXIMUM RATINGS (T_A=25°C)

SYMBOL	2N3641 2N3643 PN3641 PN3643		2N3642 PN3642		UNIT
	2N3641 2N3642 2N3643	PN3641 PN3642 PN4643			
Collector-Base Voltage	V _{CB0}	60	60		V
Collector-Emitter Voltage	V _{CEO}	30	45		V
Emitter-Base Voltage	V _{EBO}	5.0	5.0		V
Collector Current	I _C	500	500		mA
Power Dissipation Operating and Storage Junction Temperature	P _D T _J , T _{stg}	350 -55 TO +125	625 -55 TO +150		mW °C

ELECTRICAL CHARACTERISTICS (T_A=25°C)

SYMBOL	TEST CONDITIONS	2N3641 PN3641		2N3642 PN3642		2N3643 PN3643		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
I _{CES}	V _{CE} =50V		50		50		50	nA
BV _{CB0}	I _C =10μA	60		60		60		V
BV _{CES}	I _C =10μA	60		60		60		V
BV _{CEO}	I _C =10mA	30		45		30		V
BV _{EBO}	I _E =10μA	5.0		5.0		5.0		V
V _{CE(SAT)}	I _C =150mA, I _B =15mA		0.22		0.22		0.22	V
h _{FE}	V _{CE} =10V, I _C =150mA	40	120	40	120	100	300	
h _{FE}	V _{CE} =10V, I _C =500mA	15		15		25		
f _T	V _{CE} =5.0V, I _C =50mA, f=100MHz	150		150		250		MHz
C _{ob}	V _{CB} =10V, f=140kHz		8.0		8.0		8.0	pF
G _{pe}	V _{CE} =15V, R _G =140Ω, R _L =260Ω, f=30MHz, P _{IN} =40mW	10		10		10		dB
η	V _{CE} =15V, R _G =140Ω, R _L =260Ω, f=30MHz, P _{IN} =40mW	60		60		60		%
t _{on}	I _C =300mA, I _{B1} =30mA		60		60		60	ns
t _{off}	I _C =300mA, I _{B1} =I _{B2} =30mA		150		150		150	ns